

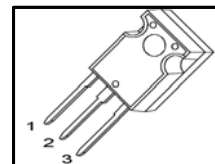
Cool MOS™ Power Transistor

Feature

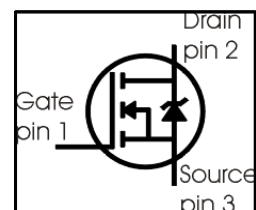
- New revolutionary high voltage technology
- Ultra low gate charge
- Periodic avalanche rated
- Extreme dv/dt rated
- High peak current capability
- Intrinsic fast-recovery body diode
- Extreme low reverse recovery charge
- Pb-free lead plating; RoHS compliant; Halogen free mold compound
- Qualified for industrial grade applications according to JEDEC⁰⁾

$V_{DS} @ T_{jmax}$	650	V
$R_{DS(on)}$	0.22	Ω
I_D	20.7	A

PG-TO247



Type	Package	Ordering Code	Marking
SPW20N60CFD	PG-TO247	Q67040-S4617	20N60CFD



Maximum Ratings

Parameter	Symbol	Value	Unit
Continuous drain current $T_C = 25\text{ °C}$ $T_C = 100\text{ °C}$	I_D	20.7 13.1	A
Pulsed drain current, t_p limited by T_{jmax}	$I_{D\text{ puls}}$	52	
Avalanche energy, single pulse $I_D = 10\text{ A}$, $V_{DD} = 50\text{ V}$	E_{AS}	690	mJ
Avalanche energy, repetitive t_{AR} limited by T_{jmax} ¹⁾ $I_D = 20\text{ A}$, $V_{DD} = 50\text{ V}$	E_{AR}	1	
Avalanche current, repetitive t_{AR} limited by T_{jmax}	I_{AR}	20	A
Reverse diode dv/dt $I_S = 20.7\text{ A}$, $V_{DS} = 480\text{ V}$, $T_j = 125\text{ °C}$	dv/dt	40	V/ns
Gate source voltage	V_{GS}	± 20	V
Gate source voltage AC ($f > 1\text{ Hz}$)	V_{GS}	± 30	
Power dissipation, $T_C = 25\text{ °C}$	P_{tot}	208	W
Operating and storage temperature	T_j, T_{stg}	-55... +150	°C

Maximum Ratings

Parameter	Symbol	Value	Unit
Drain Source voltage slope $V_{DS} = 480 \text{ V}, I_D = 20.7 \text{ A}, T_j = 125^\circ\text{C}$	dv/dt	80	V/ns
Maximum diode commutation speed $V_{DS} = 480 \text{ V}, I_D = 20.7 \text{ A}, T_j = 125^\circ\text{C}$	di_F/dt	900	A/ μs

Thermal Characteristics

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Thermal resistance, junction - case	R_{thJC}	-	-	0.6	K/W
Thermal resistance, junction - ambient, leaded	R_{thJA}	-	-	62	
Soldering temperature, wavesoldering 1.6 mm (0.063 in.) from case for 10s	T_{sold}	-	-	260	$^\circ\text{C}$

Electrical Characteristics, at $T_j=25^\circ\text{C}$ unless otherwise specified

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS}=0\text{V}, I_D=0.25\text{mA}$	600	-	-	V
Drain-Source avalanche breakdown voltage	$V_{(BR)DS}$	$V_{GS}=0\text{V}, I_D=20\text{A}$	-	700	-	
Gate threshold voltage	$V_{GS(th)}$	$I_D=1000\mu\text{A}, V_{GS}=V_{DS}$	3	4	5	
Zero gate voltage drain current	I_{DSS}	$V_{DS}=600\text{V}, V_{GS}=0\text{V},$ $T_j=25^\circ\text{C},$ $T_j=150^\circ\text{C}$	- -	2.1 1700	- -	μA
Gate-source leakage current	I_{GSS}	$V_{GS}=20\text{V}, V_{DS}=0\text{V}$	-	-	100	
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS}=10\text{V}, I_D=13.1\text{A},$ $T_j=25^\circ\text{C}$ $T_j=150^\circ\text{C}$	- -	0.19 0.51	0.22 -	Ω
Gate input resistance	R_G	$f=1\text{MHz}, \text{open Drain}$	-	0.54	-	

Electrical Characteristics , at $T_j = 25\text{ }^{\circ}\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Transconductance	g_{fs}	$V_{DS} \geq 2 \cdot I_D \cdot R_{DS(on)max}$, $I_D = 13.1\text{A}$	-	17.5	-	S
Input capacitance	C_{iss}	$V_{GS} = 0\text{V}$, $V_{DS} = 25\text{V}$, $f = 1\text{MHz}$	-	2400	-	pF
Output capacitance	C_{oss}		-	780	-	
Reverse transfer capacitance	C_{rss}		-	50	-	
Effective output capacitance, ²⁾ energy related	$C_{o(er)}$	$V_{GS} = 0\text{V}$, $V_{DS} = 0\text{V to } 480\text{V}$	-	83	-	pF
Effective output capacitance, ³⁾ time related	$C_{o(tr)}$		-	160	-	
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 380\text{V}$, $V_{GS} = 0/10\text{V}$, $I_D = 20.7\text{A}$, $R_G = 3.6\Omega$	-	12	-	ns
Rise time	t_r		-	15	-	
Turn-off delay time	$t_{d(off)}$		-	59	-	
Fall time	t_f		-	6.4	-	

Gate Charge Characteristics

Gate to source charge	Q_{gs}	$V_{DD} = 480\text{V}$, $I_D = 20.7\text{A}$	-	15	-	nC
Gate to drain charge	Q_{gd}		-	54	-	
Gate charge total	Q_g	$V_{DD} = 480\text{V}$, $I_D = 20.7\text{A}$, $V_{GS} = 0\text{ to } 10\text{V}$	-	95	124	
Gate plateau voltage	$V_{(plateau)}$	$V_{DD} = 480\text{V}$, $I_D = 20.7\text{A}$	-	7	-	V

⁰ J-STD20 and JESD22

¹ Repetitive avalanche causes additional power losses that can be calculated as $P_{AV} = E_{AR} \cdot f$.

² $C_{o(er)}$ is a fixed capacitance that gives the same stored energy as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS} .

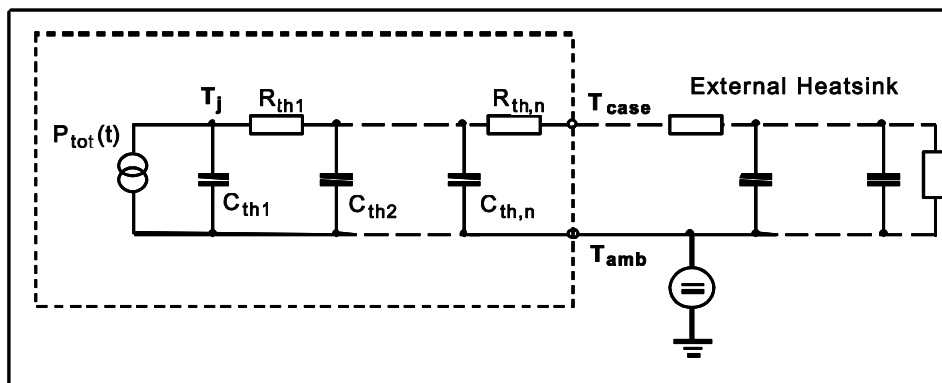
³ $C_{o(tr)}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS} .

Electrical Characteristics, at $T_J = 25\text{ }^{\circ}\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Inverse diode continuous forward current	I_S	$T_C=25^{\circ}\text{C}$	-	-	20.7	A
Inverse diode direct current, pulsed	I_{SM}		-	-	52	
Inverse diode forward voltage	V_{SD}	$V_{GS}=0\text{V}, I_F=I_S$	-	1	1.2	V
Reverse recovery time	t_{rr}	$V_R=480\text{V}, I_F=I_S, di_F/dt=100\text{A}/\mu\text{s}$	-	150	-	ns
Reverse recovery charge	Q_{rr}		-	1	-	μC
Peak reverse recovery current	I_{rrm}		-	13	-	A
Peak rate of fall of reverse recovery current	di_{rr}/dt		-	1400	-	$\text{A}/\mu\text{s}$

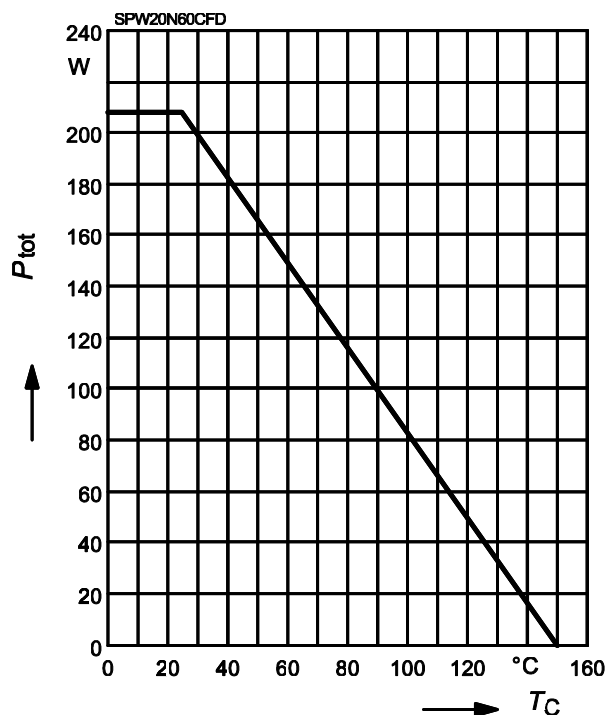
Typical Transient Thermal Characteristics

Symbol	Value	Unit	Symbol	Value	Unit
	typ.			typ.	
Thermal resistance			Thermal capacitance		
R_{th1}	0.007686	K/W	C_{th1}	0.0003764	Ws/K
R_{th2}	0.015		C_{th2}	0.001412	
R_{th3}	0.029		C_{th3}	0.001932	
R_{th4}	0.114		C_{th4}	0.005299	
R_{th5}	0.136		C_{th5}	0.012	
R_{th6}	0.059		C_{th6}	0.091	



1 Power dissipation

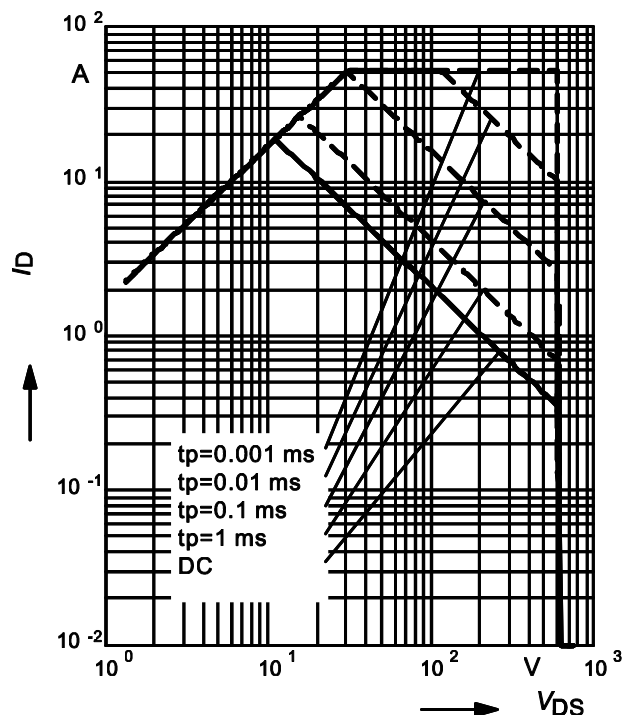
$$P_{\text{tot}} = f(T_C)$$



2 Safe operating area

$$I_D = f(V_{DS})$$

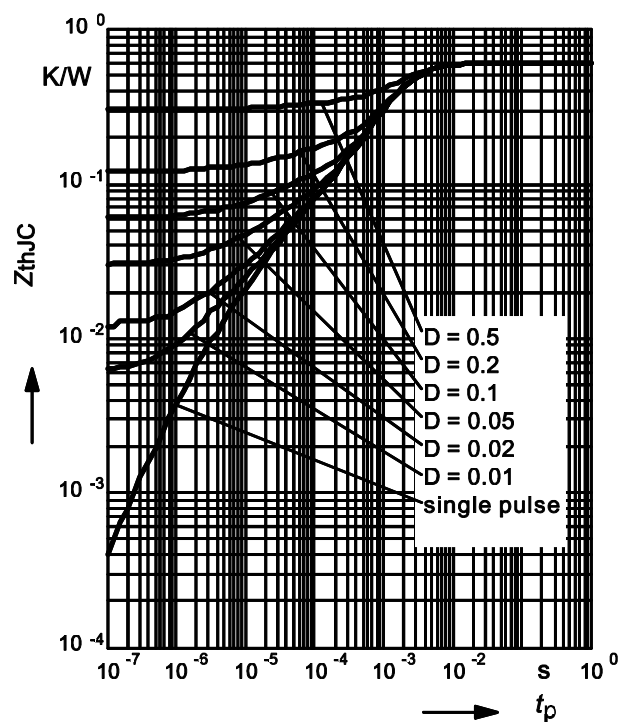
parameter : $D = 0$, $T_C = 25^\circ\text{C}$



3 Transient thermal impedance

$$Z_{\text{thJC}} = f(t_p)$$

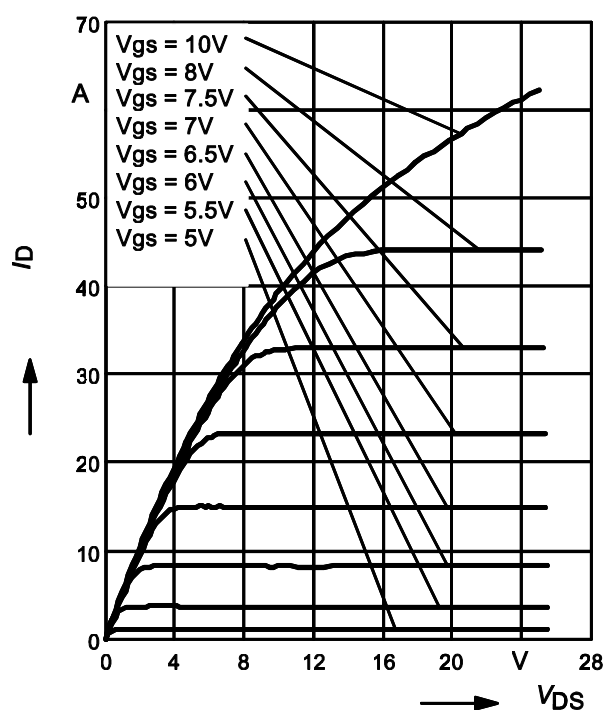
parameter: $D = t_p/T$



4 Typ. output characteristic

$$I_D = f(V_{DS}); T_J = 25^\circ\text{C}$$

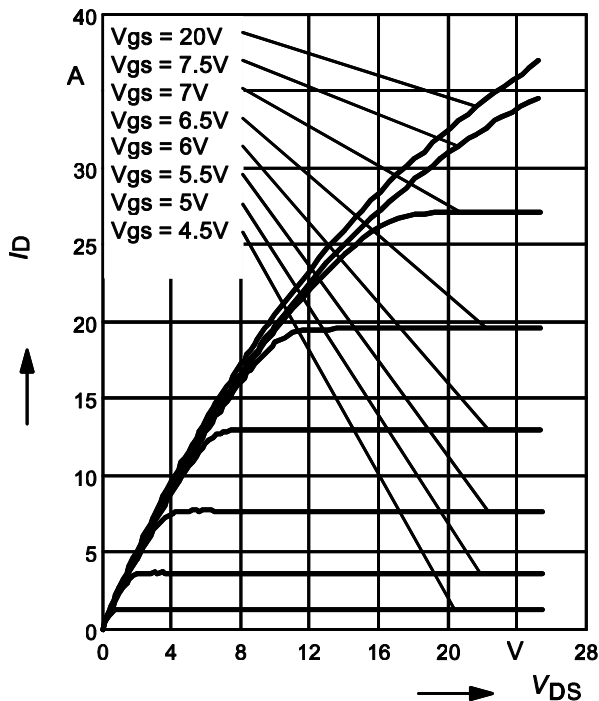
parameter: $t_p = 10 \mu\text{s}$, V_{GS}



5 Typ. output characteristic

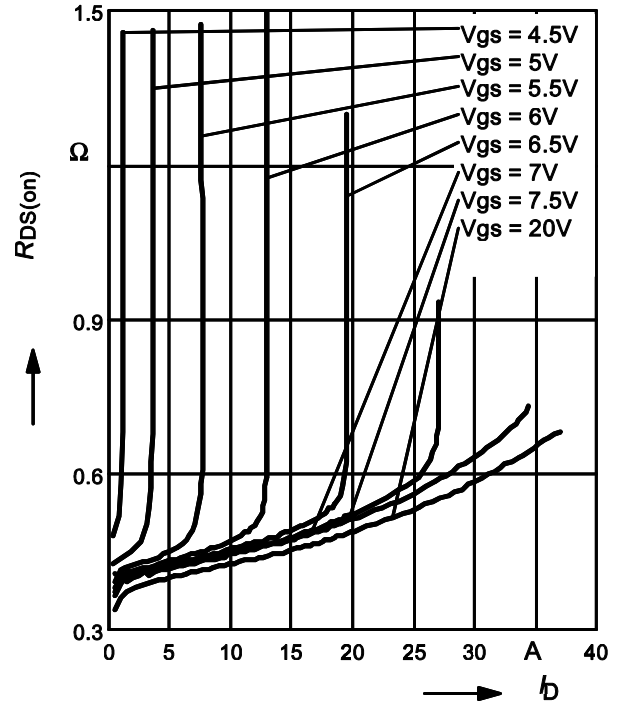
$$I_D = f(V_{DS}); T_J = 150^\circ\text{C}$$

parameter: $t_p = 10 \mu\text{s}$, V_{GS}


6 Typ. drain-source on resistance

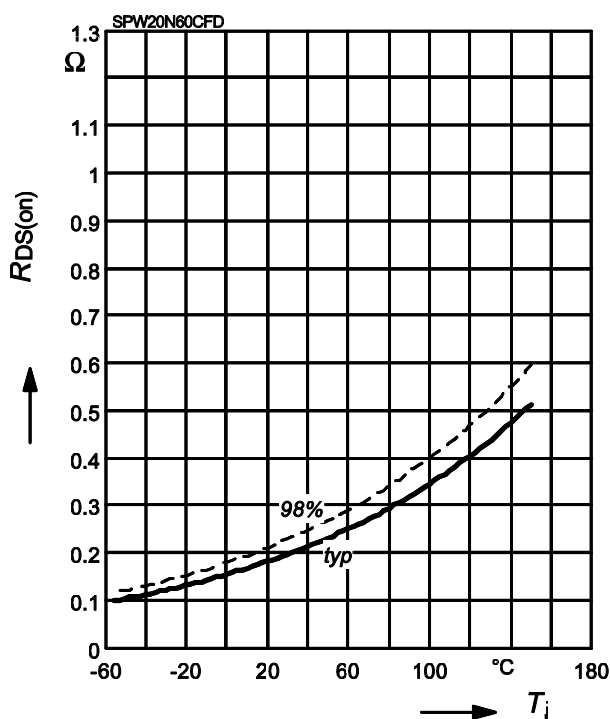
$$R_{DS(on)} = f(I_D)$$

parameter: $T_J = 150^\circ\text{C}$, V_{GS}


7 Drain-source on-state resistance

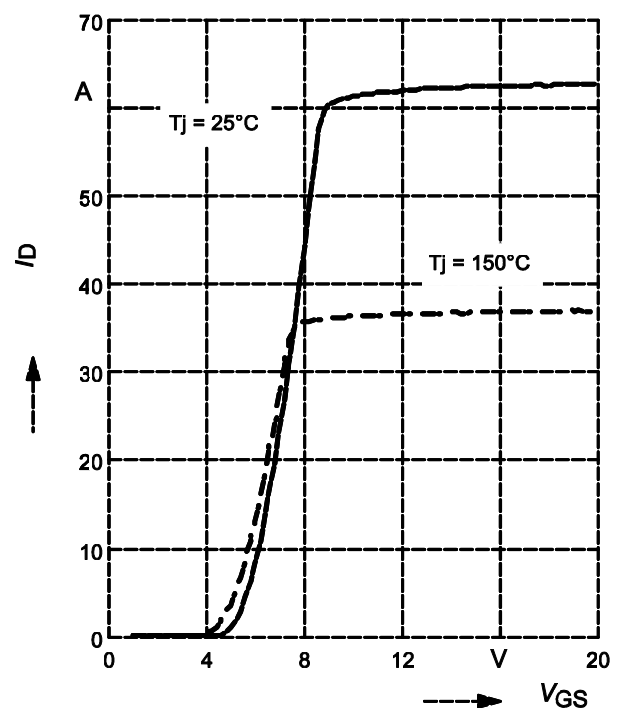
$$R_{DS(on)} = f(T_J)$$

parameter: $I_D = 13.1 \text{ A}$, $V_{GS} = 10 \text{ V}$


8 Typ. transfer characteristics

$$I_D = f(V_{GS}); V_{DS} \geq 2 \times I_D \times R_{DS(on)max}$$

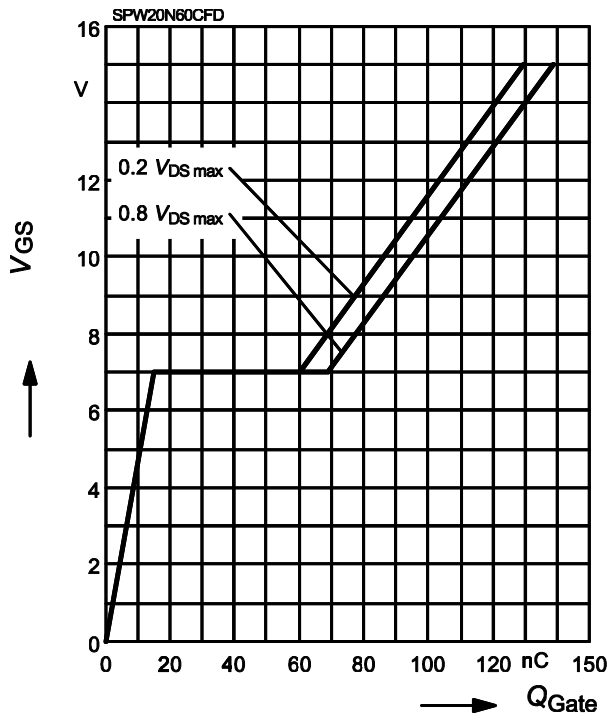
parameter: $t_p = 10 \mu\text{s}$



9 Typ. gate charge

$$V_{GS} = f(Q_{Gate})$$

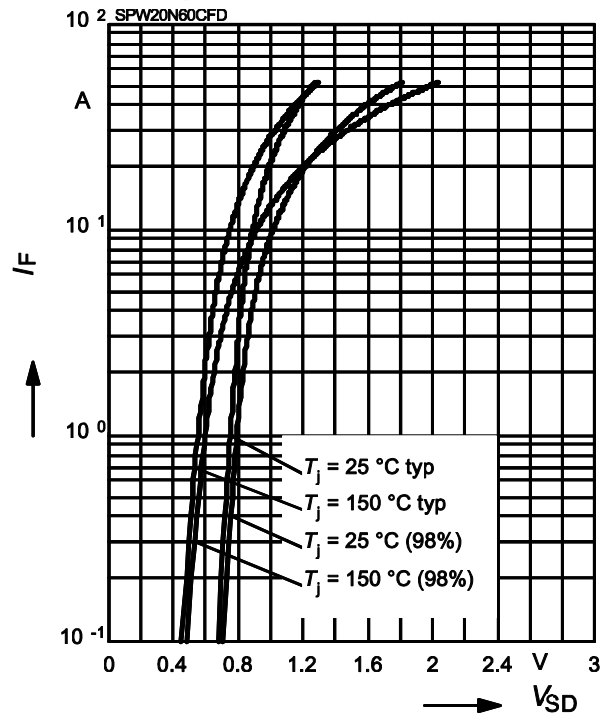
parameter: $I_D = 20.7 \text{ A}$ pulsed



10 Forward characteristics of body diode

$$I_F = f(V_{SD})$$

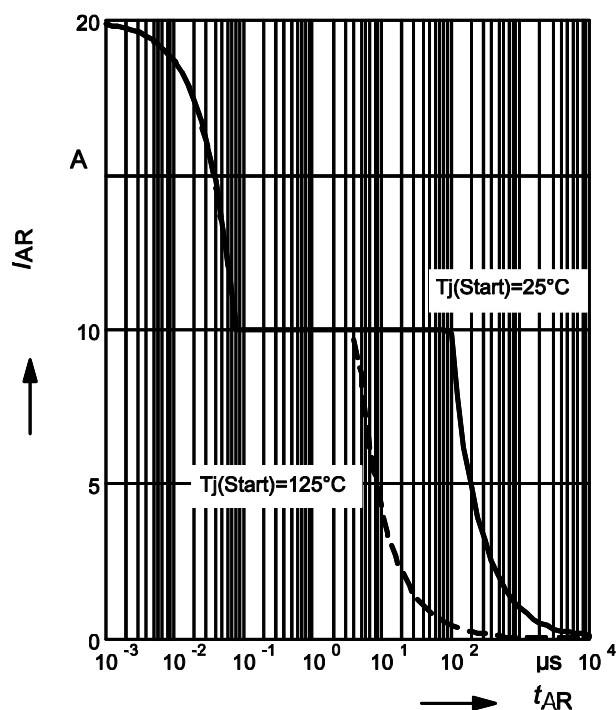
parameter: $T_j, t_p = 10 \mu\text{s}$



11 Avalanche SOA

$$I_{AR} = f(t_{AR})$$

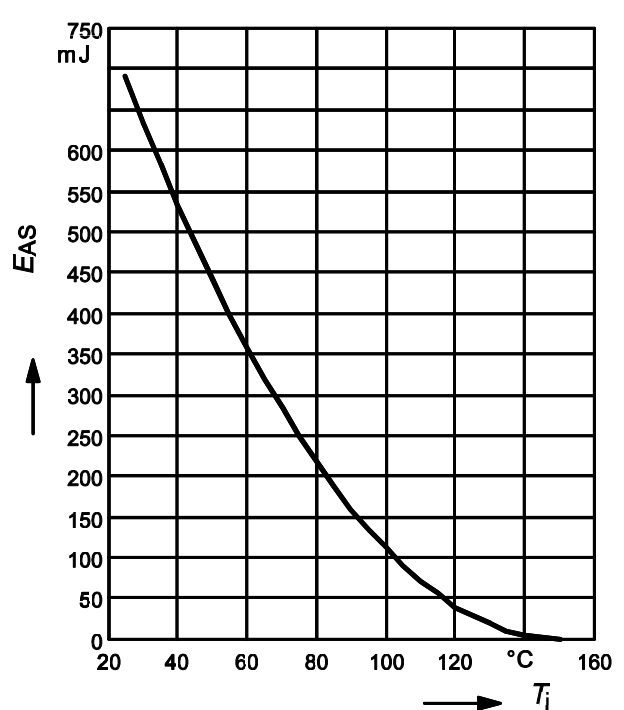
par.: $T_j \leq 150 \text{ °C}$



12 Avalanche energy

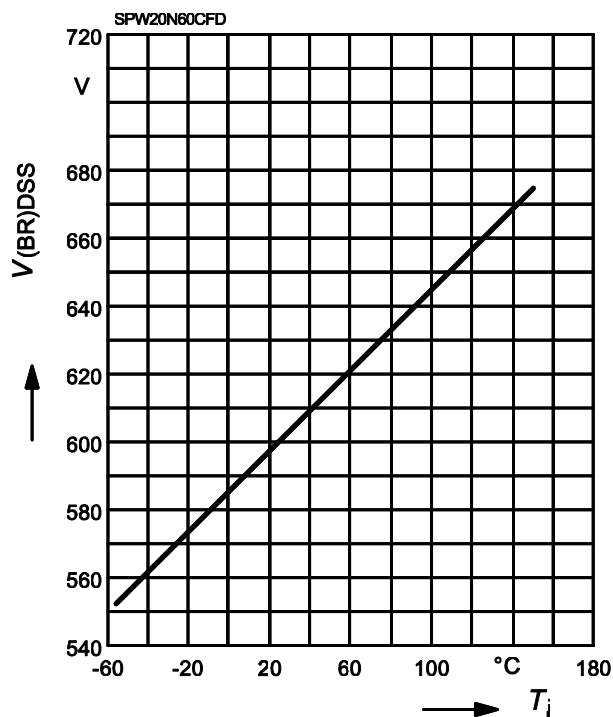
$$E_{AS} = f(T_j)$$

par.: $I_D = 10 \text{ A}, V_{DD} = 50 \text{ V}$



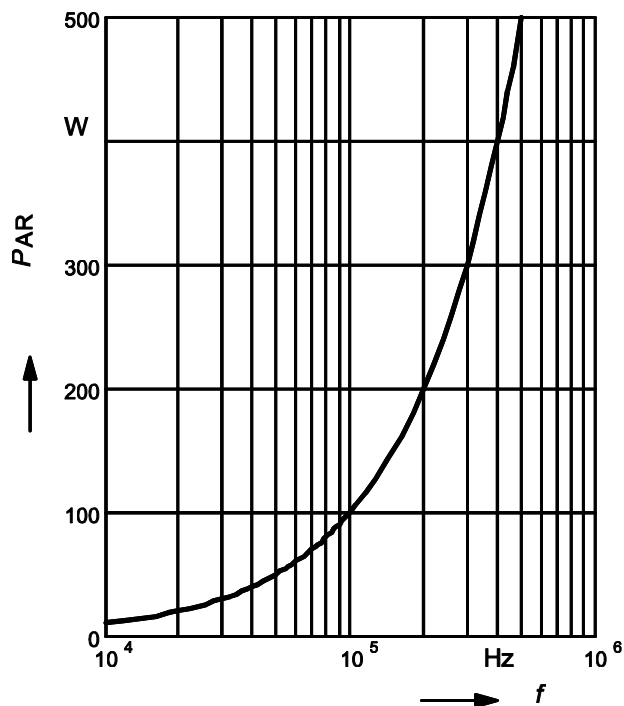
13 Drain-source breakdown voltage

$$V_{(BR)DSS} = f(T_j)$$


14 Avalanche power losses

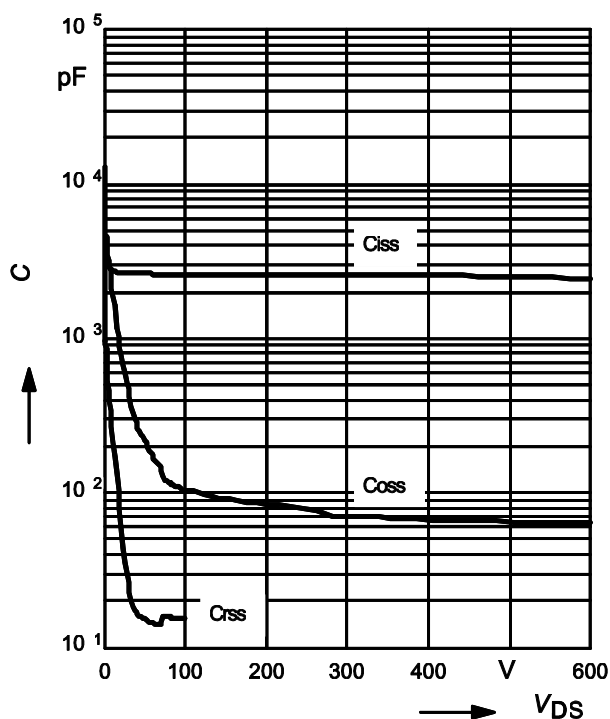
$$P_{AR} = f(f)$$

parameter: $E_{AR}=1\text{mJ}$

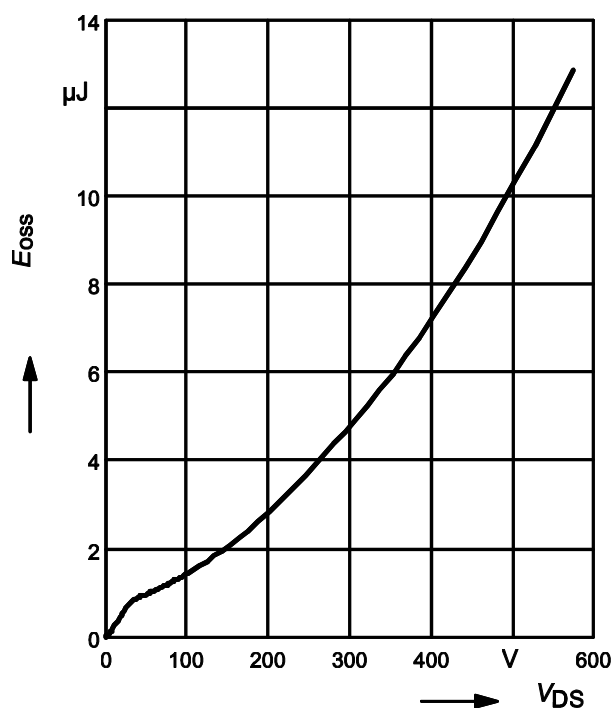

15 Typ. capacitances

$$C = f(V_{DS})$$

parameter: $V_{GS}=0\text{V}$, $f=1\text{ MHz}$


16 Typ. C_{OSS} stored energy

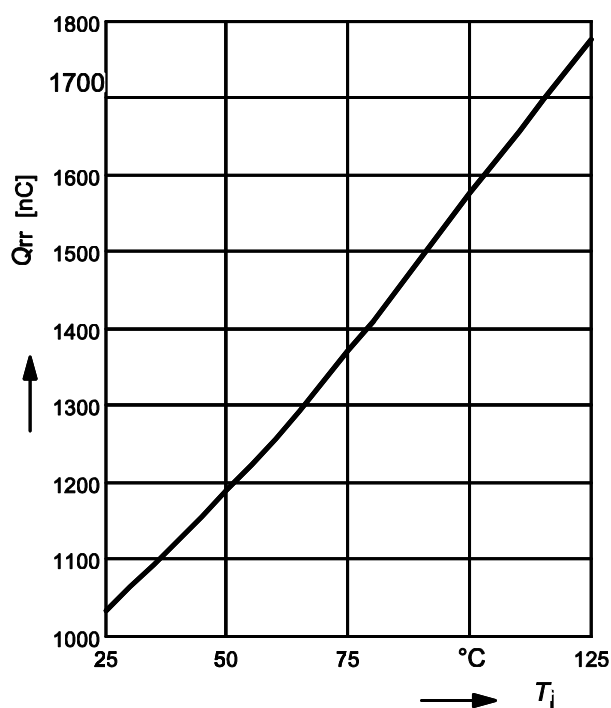
$$E_{OSS}=f(V_{DS})$$



17 Typ. reverse recovery charge

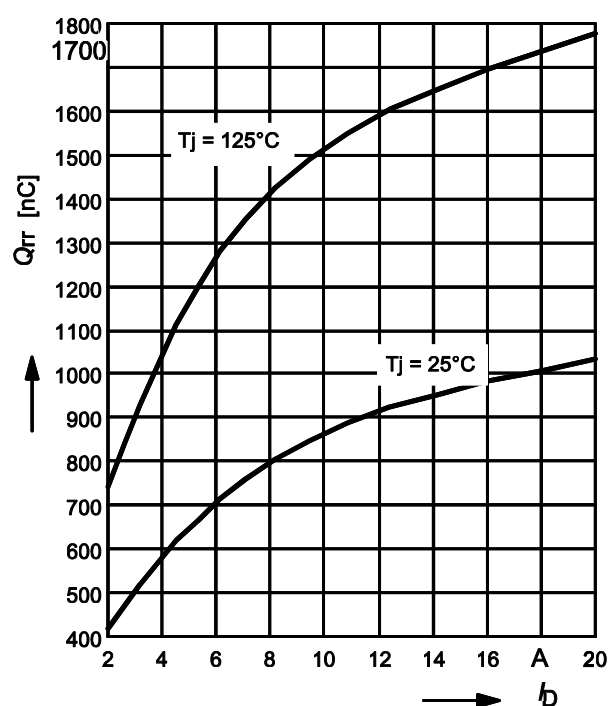
$$Q_{rr} = f(T_J)$$

parameter: $I_D = 20.7 \text{ A}$


18 Typ. reverse recovery charge

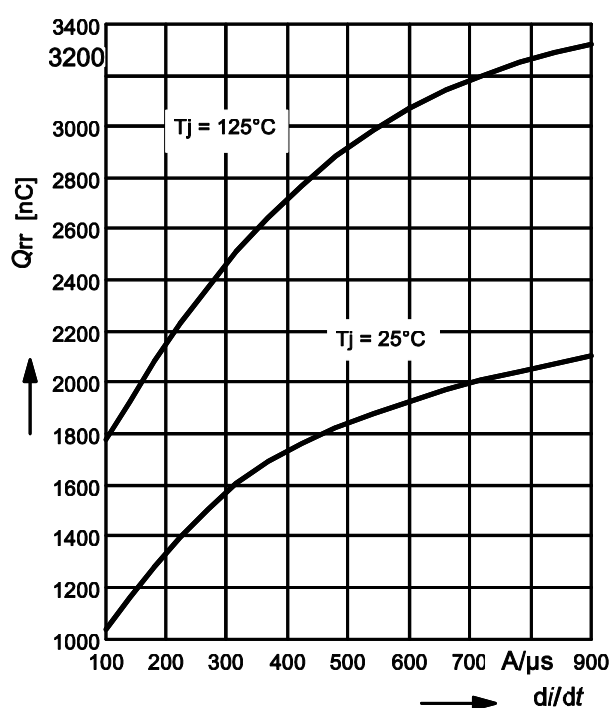
$$Q_{rr} = f(I_D)$$

parameter: $di/dt = 100 \text{ A/}\mu\text{s}$

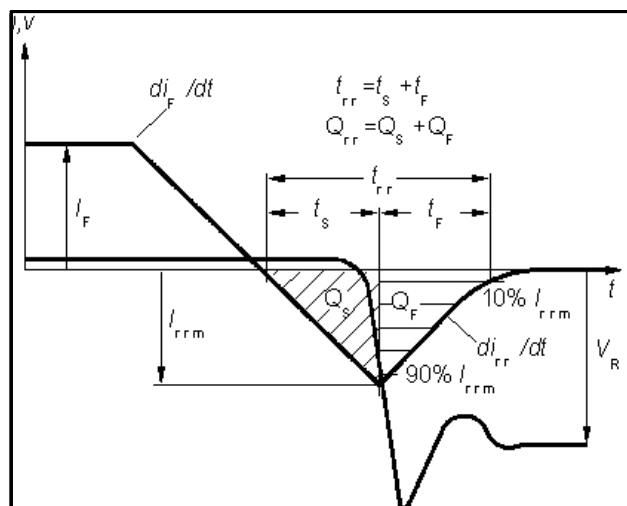

19 Typ. reverse recovery charge

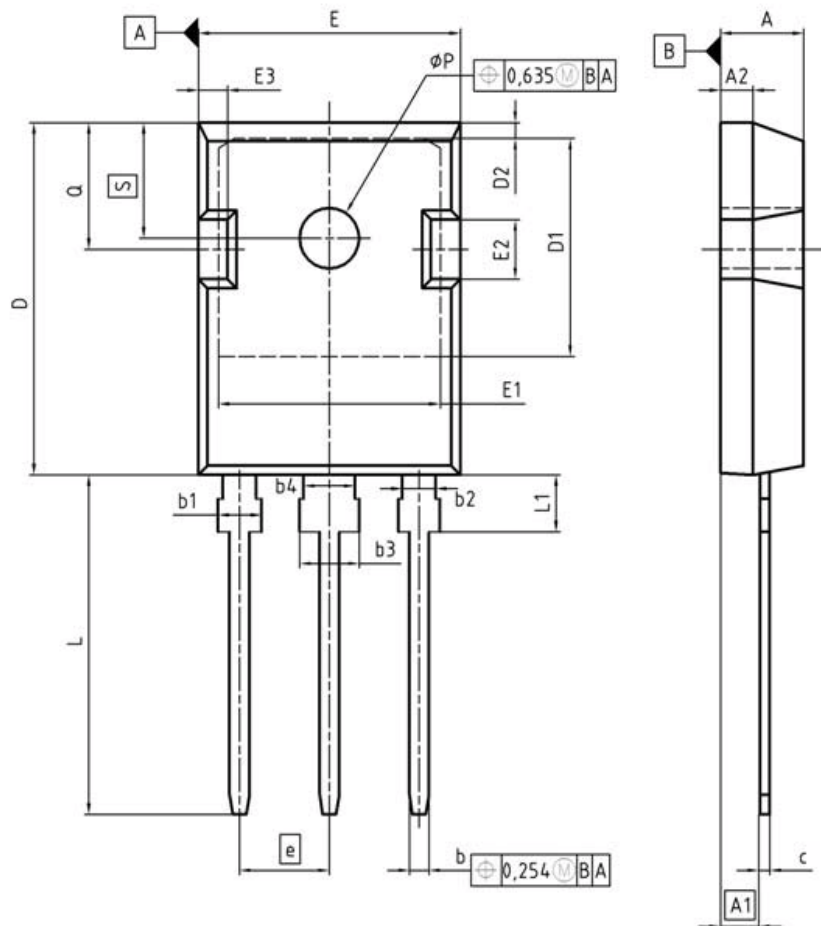
$$Q_{rr} = f(di/dt)$$

parameter: $I_D = 20.7 \text{ A}$

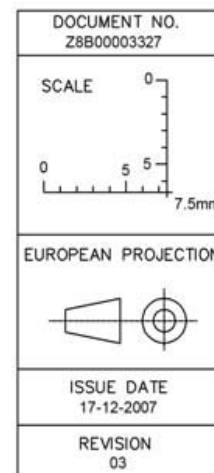


Definition of diodes switching characteristics





DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.90	5.16	0.193	0.203
A1	2.27	2.53	0.089	0.099
A2	1.85	2.11	0.073	0.083
b	1.07	1.33	0.042	0.052
b1	1.90	2.41	0.075	0.095
b2	1.90	2.16	0.075	0.085
b3	2.87	3.38	0.113	0.133
b4	2.87	3.13	0.113	0.123
c	0.55	0.68	0.022	0.027
D	20.82	21.10	0.820	0.831
D1	16.25	17.65	0.640	0.695
D2	1.05	1.35	0.041	0.053
E	15.70	16.03	0.618	0.631
E1	13.10	14.15	0.516	0.557
E2	3.68	5.10	0.145	0.201
E3	1.68	2.60	0.066	0.102
e	5.44		0.214	
N	3		3	
L	19.80	20.31	0.780	0.799
L1	4.17	4.47	0.164	0.176
eP	3.50	3.70	0.138	0.146
Q	5.49	6.00	0.216	0.236
S	6.04	6.30	0.238	0.248



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Infineon Technologies AG
81726 Munich, Germany
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1 New package outlines TO-247

Assembly capacity extension for CoolMOSTM technology products assembled in lead-free package
PG-TO247-3 at subcontractor ASE (Weihai) Inc., China (Changes are marked in blue.)

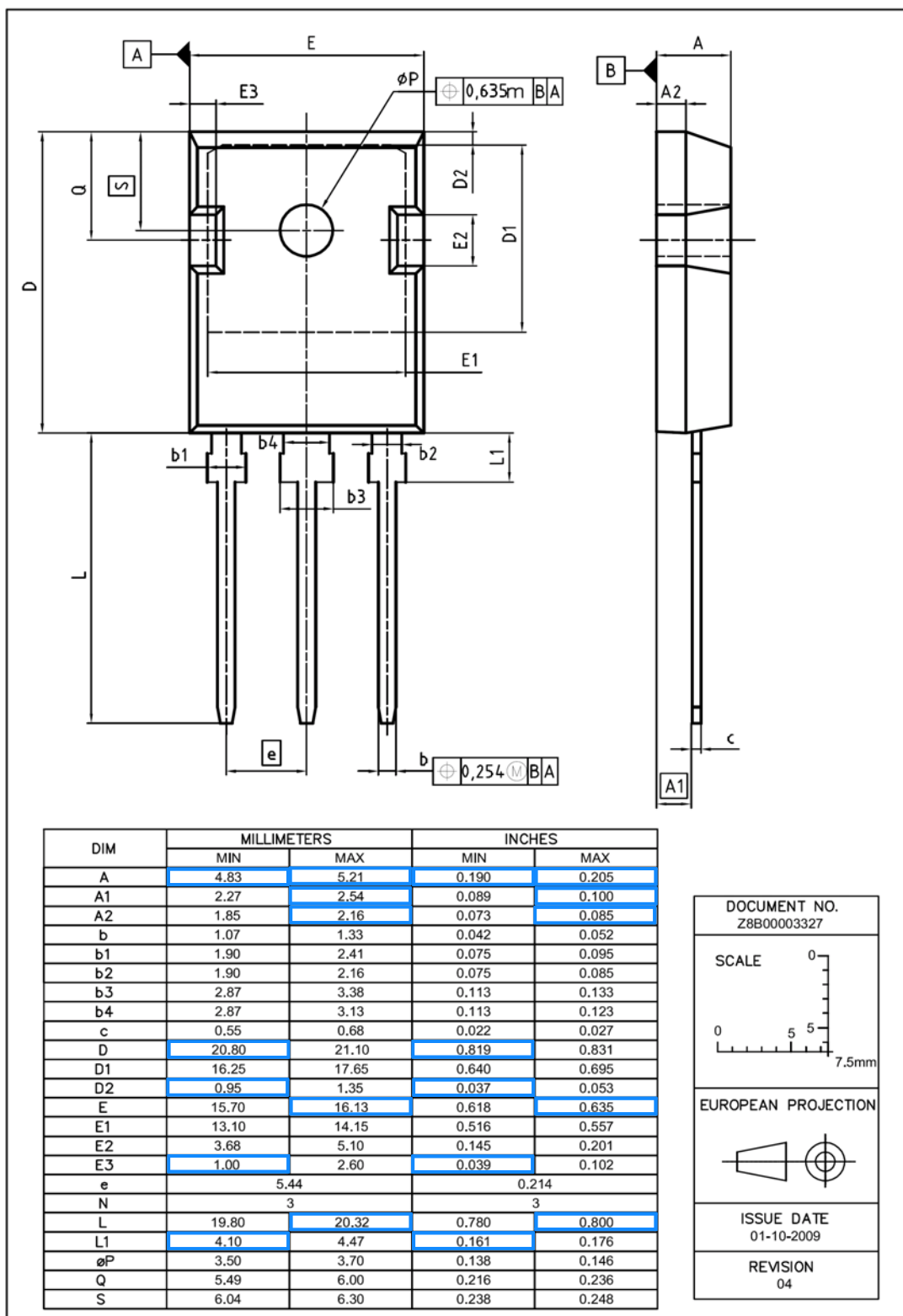


Figure 1 Outlines TO-247, dimensions in mm/inches